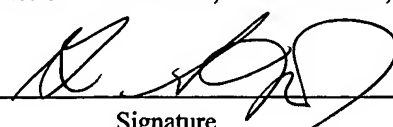




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Graham S. Jones, II; Reg. No. 20,429  25 August 2005  
Name of Person Making Deposit Signature Date

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Inventors:	<b>Tina J. Wagner et al.</b>	Date:	<b>25 August 2005</b>
Serial No.:	<b>10/605,100</b>	Art Unit:	<b>2818</b>
Filing Date:	<b>09 September 2003</b>	Examiner:	<b>David Vu</b>
Confirmation No.:	<b>2099</b>	Docket No.:	<b>FIS920030249US1</b>
Title:	<b>A Raised Source Drain MOSFET with Notch Formed on Top of Gate Structure Filled with a Dielectric Plug</b>	Attorney:	<b>Graham S. Jones, II 42 Barnard Avenue Poughkeepsie, NY 12603-5023</b>

**AMENDMENT**

**The Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450**

**Your Honor:**

**In response to the Office Action of 26 May 2005, please amend the above-identified application as follows:**

<b>Amendments to the Abstract</b>	<b>begin on page 2 of this paper</b>
<b>Amendments to the Specification</b>	<b>begin on page 3 of this paper</b>
<b>Amendments to the Claims</b>	<b>begin on page 6 of this paper.</b>
<b>Remarks/Arguments</b>	<b>begin on page 11 of this paper.</b>